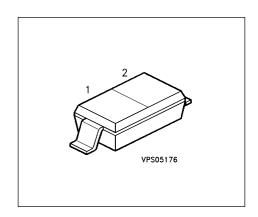


Silicon Schottky Diode

• Low Barrier diode for detectors up to GHz frequencies



ESD: Electro**S**tatic **D**ischarge sensitive device, observe handling precautions!

Туре	Marking	Ordering Code	Pin Configuration			Package
BAT 62-03W	L	Q62702-A1028	1 = A	2 = C		SOD-323

Maximum Ratings

Parameter	Symbol	Values	Unit	
Diode reverse voltage	V_{R}	40	V	
Forward current	I _F	40	mA	
Junction temperature	$T_{\rm j}$	150	°C	
Storage temperature	T _{stg}	- 55 + 150		
Total power dissipation <i>T</i> _S ≤ 85°C	P _{tot}	100	mW	

Thermal Resistance

Junction ambient 1)	R_{thJA}	≤ 650	K/W
Junction - soldering point	R _{thJS}	≤ 810	

¹⁾ Package mounted on epoxy pcb 15mm x 16.7mmm x 0.7mm

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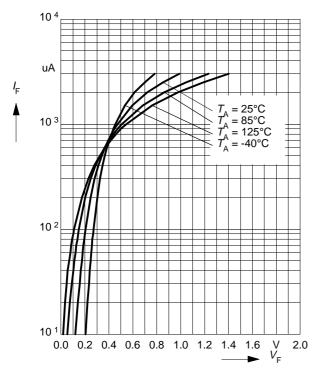
Electrical Characteristics at T_A =25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					·
Reverse current	I_{R}				μA
V_{R} = 40 V, T_{A} = 25 °C		-	-	10	
Forward voltage	V_{F}				V
$I_{F} = 2 \; mA$		-	0.58	1	
AC Characteristics	•		<u>.</u>		•
Diode capacitance	C_{T}				pF
$V_{R} = 0$, $f = 1$ MHz		-	0.35	0.6	
Case capacitance	$C_{\mathbb{C}}$				
f = 1 MHz		-	0.1	-	
Differential resistance	R_0				kΩ
$V_{R} = 0$, $f = 10 \text{ kHz}$		-	225	-	
Series inductance chip to ground	L _s	-	2	-	nH

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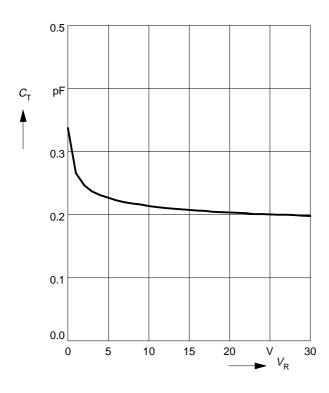
Forward current $I_F = f(V_F)$

 T_A = parameter



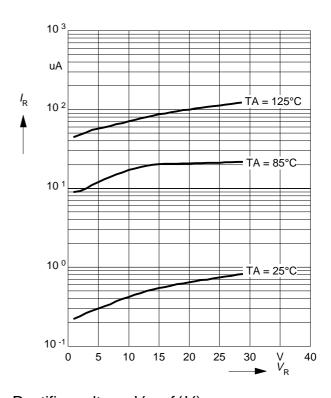
Diode capacitance $C_T = f(V_R)$

f = 1MHz



Leakage current $I_R = f(V_R)$

 T_A = Parameter



Rectifier voltage $V_0 = f(V_i)$

f = 900 MHz

 R_{L} = parameter in Ω

